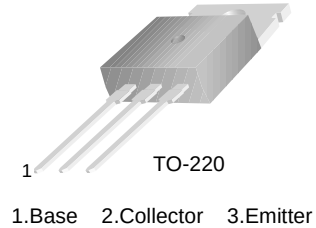


BU407/407H

BU407/407H

High Voltage Switching

- Use In Horizontal Deflection Output Stage



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	330	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current (DC)	7	A
I_{CP}	Collector Current (Pulse)	10	A
I_B	Base Current	4	A
P_C	Collector Dissipation ($T_C=25^\circ\text{C}$)	60	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
I_{CES}	Collector Cut-off Current	$V_{CE} = 330\text{V}, V_{BE} = 0$ $V_{CE} = 200\text{V}, V_{BE} = 0$ $V_{CE} = 200\text{V}, V_{BE} = 0 @ T_C = 150^\circ\text{C}$		5 100 1	mA μA mA
I_{EBO}	Emitter Cut-off Current	$V_{BE} = 6\text{V}, I_C = 0$		1	mA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage : BU407 : BU407H	$I_C = 5\text{A}, I_B = 0.5\text{A}$ $I_C = 5\text{A}, I_B = 0.8\text{A}$		1 1	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage : BU407 : BU407H	$I_C = 5\text{A}, I_B = 0.5\text{A}$ $I_C = 5\text{A}, I_B = 0.8\text{A}$		1.2 1.2	V V
f_T	Current Gain Bandwidth Product	$V_{CE} = 10\text{V}, I_C = 0.5\text{A}$	10		MHz
t_{OFF}	Turn OFF Time : BU407 : BU407H	$I_C = 5\text{A}, I_B = 0.5\text{A}$ $I_C = 5\text{A}, I_B = 0.8\text{A}$		0.75 0.4	μs μs

Typical Characteristics

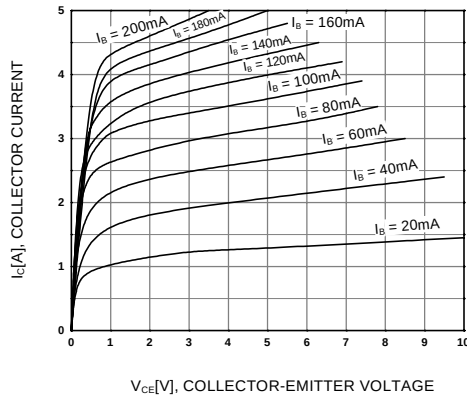


Figure 1. Static Characteristic

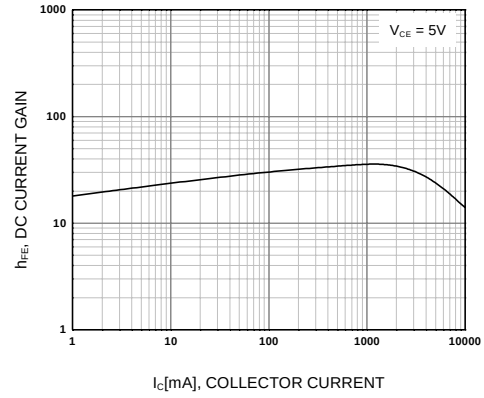


Figure 2. DC current Gain

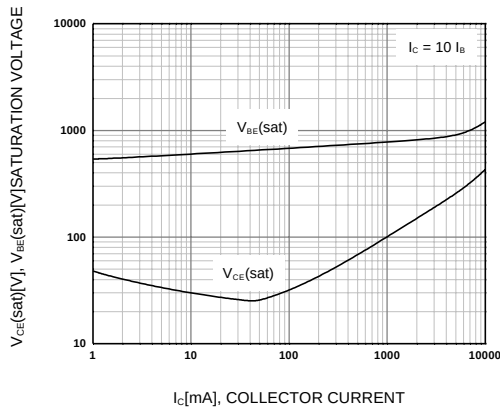


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

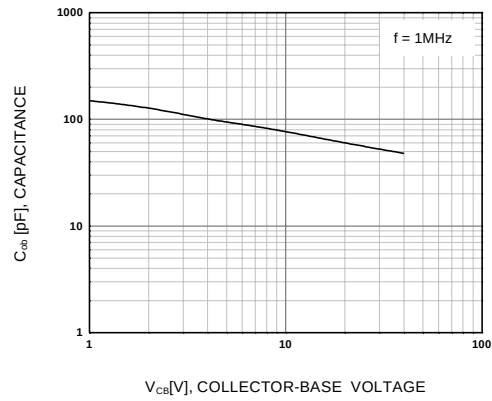


Figure 4. Collector Output Capacitance

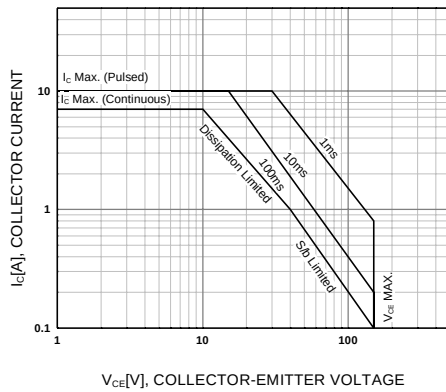


Figure 5. Safe Operating Area

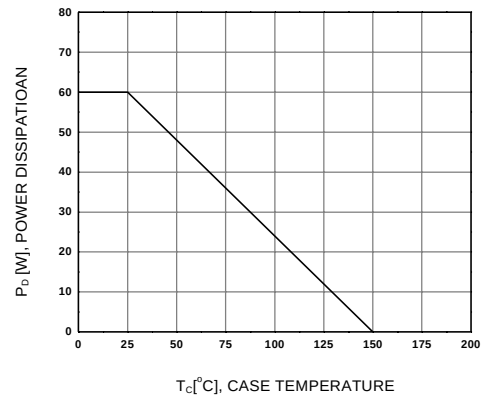
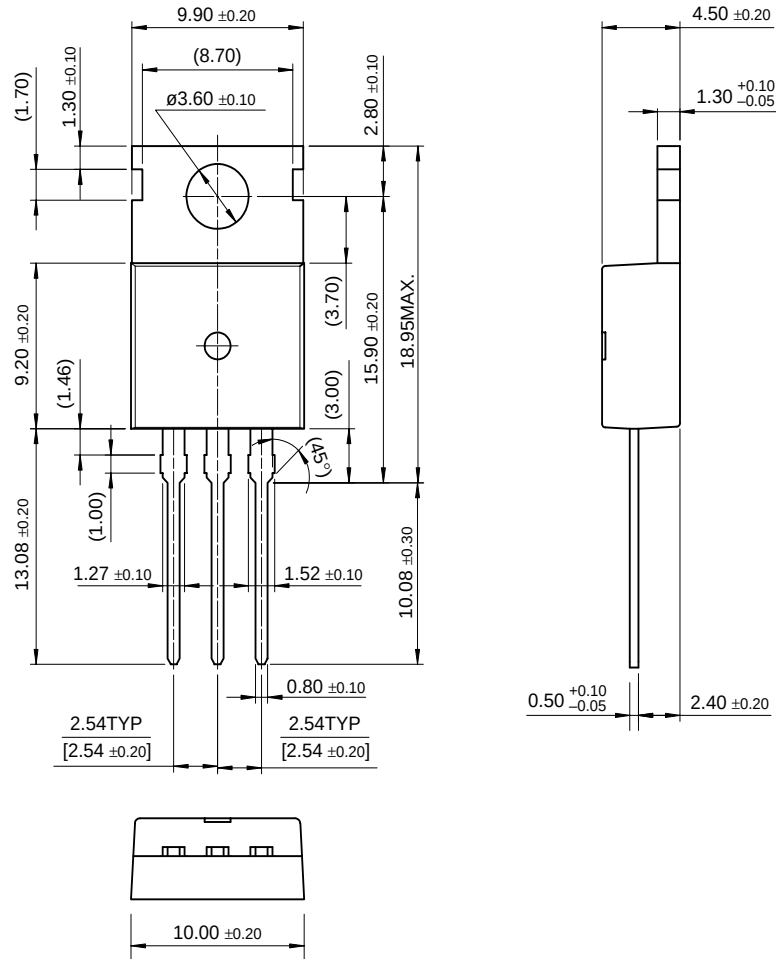


Figure 6. Power Derating

Package Dimensions

TO-220



Dimensions in Millimeters